High-Speed USB 2.0 (480 Mbps) DPDT Switches

The NL3HS2222 is a DPDT switch optimized for high–speed USB 2.0 applications within portable systems. It features ultra–low on capacitance, $C_{\rm ON}=7.5$ pF (typ), and a bandwidth above 950 MHz. It is optimized for applications that use a single USB interface connector to route multiple signal types. The $C_{\rm ON}$ and $R_{\rm ON}$ of both channels are suitably low to allow the NL3HS2222 to pass any speed USB data or audio signals going to a moderately resistive terminal such as an external headset. The device is offered in a UQFN10 1.4 mm x 1.8 mm package.

Features

- Optimized Flow-Through Pinout
- R_{ON} : 5.0 Ω Typ @ $V_{CC} = 4.2 \text{ V}$
- C_{ON} : 7.5 pF Typ @ V_{CC} = 3.3 V
- V_{CC} Range: 1.65 V to 4.5 V
- Typical Bandwidth: 950 MHz
- 1.4 mm x 1.8 mm x 0.50 mm UQFN10
- OVT on Common Signal Pins D+/D- up to 5.25 V
- 8 kV HBM ESD Protection on All Pins
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

Typical Applications

- High Speed USB 2.0 Data
- Mobile Phones
- Portable Devices

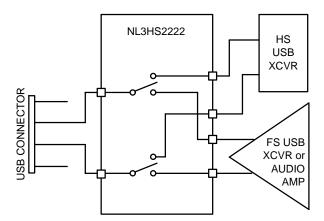


Figure 1. Application Diagram



ON Semiconductor®

www.onsemi.com

MARKING DIAGRAM



UQFN10 CASE 488AT



AV = Device Code

M = Date Code

Pb-Free Device

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
NL3HS2222MUTBG	UQFN10 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

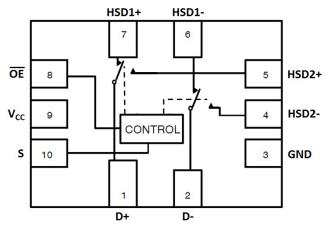


Figure 2. Pin Connections and Logic Diagram (Top View)

Table 1. PIN DESCRIPTION

Pin	Function
S	Control Input
ŌĒ	Output Enable
HSD1+, HSD1-, HSD2+, HSD2-, D+, D-	Data Ports

Table 2. TRUTH TABLE

ŌĒ	s	HSD1+, HSD1-	HSD2+, HSD2-
1	X	OFF	OFF
0	0	ON	OFF
0	1	OFF	ON

MAXIMUM RATINGS

Symbol	Pins	Parameter	Value	Unit
V _{CC}	V _{CC}	Positive DC Supply Voltage	-0.5 to +5.5	V
V _{IS}	HSDn+, HSDn-	Analog Signal Voltage	-0.5 to V_{CC} + 0.3	V
-	D+, D-	1	-0.5 to +5.25	
V_{IN}	S, OE Control Input Voltage, Output Enable Voltage		-0.5 to +5.5	V
I _{CC}	V _{CC}	Positive DC Supply Current	50	mA
T _S		Storage Temperature	-65 to +150	°C
I _{IS_CON}	HSDn+, HSDn-, D+, D-	Analog Signal Continuous Current–Closed Switch	±300	mA
I _{IS_PK}	HSDn+, HSDn-, D+, D-	Analog Signal Continuous Current 10% Duty Cycle	±500	mA
I _{IN}	S, OE	Control Input Current, Output Enable Current	±20	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

RECOMMENDED OPERATING CONDITIONS

Symbol	Pins	Parameter	Min	Max	Unit
V_{CC}		Positive DC Supply Voltage	1.65	4.5	V
V _{IS}	HSDn+, HSDn–	Analog Signal Voltage	GND	V _{CC}	V
	D+, D-		GND	4.5	1
V_{IN}	S, OE	Control Input Voltage, Output Enable Voltage	GND	V _{CC}	V
T _A		Operating Temperature	-40	+85	°C

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

ESD PROTECTION

Symbol	Parameter	Value	Unit
ESD	Human Body Model – All Pins	8.0	kV

DC ELECTRICAL CHARACTERISTICS

CONTROL INPUT, OUTPUT ENABLE VOLTAGE (Typical: T = 25°C)

					–40°C to +85°C			
Symbol	Pins	Parameter	Test Conditions	V _{CC} (V)	Min	Тур	Max	Unit
V _{IH}	S, ŌE	Control Input, Output Enable HIGH Voltage (See Figure 11)		2.7 3.3 4.2	1.25 1.3 1.4	-	-	V
V _{IL}	S, OE	Control Input, Output Enable LOW Voltage (See Figure 11)		2.7 3.3 4.2	-	-	0.35 0.4 0.5	V
I _{IN}	S, OE	Current Input, Output Enable Leakage Current	$0 \le V_{IS} \le V_{CC}$	1.65 – 4.5	-	-	±1.0	μΑ

SUPPLY CURRENT AND LEAKAGE (Typical: T = 25° C, $V_{CC} = 3.3 \text{ V}$)

					-40°C to +85°C			
Symbol	Pins	Parameter	Test Conditions	V _{CC} (V)	Min	Тур	Max	Unit
I _{CC}	V _{CC}	Quiescent Supply Current	$0 \le V_{IS} \le V_{CC}$; $I_D = 0 \text{ A}$ $0 \le V_{IS} \le V_{CC} - 0.5 \text{ V}$	1.65 – 3.6 3.6 – 4.5	- -	- -	1.0 1.0	μΑ
I _{OZ}		OFF State Leakage	$0 \le V_{IS} \le V_{CC}$	1.65 – 4.5	-	±0.1	±1.0	μΑ
l _{OFF}	D+, D-	Power OFF Leakage Current	$0 \le V_{IS} \le V_{CC}$	0	_	-	±1.0	μΑ

LIMITED V_{IS} SWING ON RESISTANCE (Typical: T = 25°C)

					–40°C to +85°C			
Symbol	Pins	Parameter	Test Conditions	V _{CC} (V)	Min	Тур	Max	Unit
R _{ON}		On–Resistance (Note 1)	I _{ON} = 8 mA V _{IS} = 0 V to 0.4 V	2.7 3.3 4.2	-	6.0 5.5 5.0	8.6 7.6 7.0	Ω
R _{FLAT}		On–Resistance Flatness (Notes 1 and 2)	I _{ON} = 8 mA V _{IS} = 0 V to 0.4 V	2.7 3.3 4.2	-	0.55 0.30 0.20	-	Ω
ΔR _{ON}		On–Resistance Matching (Notes 1 and 3)	I _{ON} = 8 mA V _{IS} = 0 V to 0.4 V	2.7 3.3 4.2	-	0.60 0.60 0.60	-	Ω

^{1.} Guaranteed by design.

FULL V_{IS} SWING ON RESISTANCE (Typical: T = 25°C)

					–40°C to +85°C			
Symbol	Pins	Parameter	Test Conditions	V _{CC} (V)	Min	Тур	Max	Unit
R _{ON}		On-Resistance	I _{ON} = 8 mA V _{IS} = 0 V to V _{CC}	2.7 3.3 4.2	-	10 8.0 7.0	13.5 9.75 8.50	Ω
R _{FLAT}		On–Resistance Flatness (Notes 4 and 5)	I _{ON} = 8 mA V _{IS} = 0 V to V _{CC}	2.7 3.3 4.2	-	4.5 3.0 2.5	-	Ω
ΔR _{ON}		On–Resistance (Note 4 and 6)	$I_{ON} = 8 \text{ mA}$ $V_{IS} = 0 \text{ V to } V_{CC}$	2.7 3.3 4.2	-	0.60 0.60 0.60	-	Ω

^{4.} Guaranteed by design.

Flatness is defined as the difference between the maximum and minimum value of On–Resistance as measured over the specified analog signal ranges.

^{3.} $\Delta R_{ON} = R_{ON(max)} - R_{ON(min)}$ between HSD1+ and HSD1- or HSD2+ and HSD2-.

^{5.} Flatness is defined as the difference between the maximum and minimum value of On–Resistance as measured over the specified analog signal ranges.

^{6.} $\Delta R_{ON} = R_{ON(max)} - R_{ON(min)}$ between HSD1+ and HSD1- or HSD2+ and HSD2-.

AC ELECTRICAL CHARACTERISTICS

TIMING/FREQUENCY (Typical: T = 25°C, V_{CC} = 3.3 V, R_L = 50 Ω , C_L = 35 pF, f = 1 MHz)

					-40°C to +85°C			
Symbol	Pins	Parameter	Test Conditions	V _{CC} (V)	Min	Тур	Max	Unit
t _{ON}	Closed to Open	Turn-ON Time (See Figures 4 and 5)		1.65 – 4.5	-	13.0	30.0	ns
t _{OFF}	Open to Closed	Turn-OFF Time (See Figures 4 and 5)		1.65 – 4.5	-	12.0	25.0	ns
T _{BBM}		Break-Before-Make Time (See Figure 3)		1.65 – 4.5	2.0	-	-	ns
BW		-3 dB Bandwidth (See Figure 10)	C _L = 5 pF	1.65 – 4.5	-	950	-	MHz

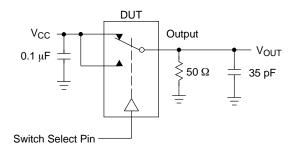
ISOLATION (Typical: T = 25°C, V_{CC} = 3.3 V, R_L = 50 Ω , C_L = 5 pF)

					-40°C to +85°C			
Symbol	Pins	Parameter	Test Conditions	V _{CC} (V)	Min	Тур	Max	Unit
O _{IRR}	Open	OFF-Isolation (See Figure 6)	f = 240 MHz	1.65 – 4.5	-	-22	-	dB
X _{TALK}	HSDn+ to HSDn-	Non-Adjacent Channel Crosstalk	f = 240 MHz	1.65 – 4.5	-	-24	-	dB

 $\textbf{CAPACITANCE} \text{ (Typical: T = 25°C, V}_{CC} = 3.3 \text{ V, R}_{L} = 50 \ \Omega, C_{L} = 5 \text{ pF)}$

				-40°C to +85°C			
Symbol	Pins	Parameter	Test Conditions	Min	Тур	Max	Unit
C _{IN}	S, OE	Control Pin, Output Enable Input Capacitance	V _{CC} = 0 V, f = 1 MHz	-	1.5	_	pF
			V _{CC} = 0 V, f = 10 MHz	_	1.0	_	
C _{ON}	D+ to HSD1+ or HSD2+	ON Capacitance	V _{CC} = 3.3 V; OE = 0 V, f = 1 MHz S = 0 V or 3.3 V	_	7.5	-	
			V _{CC} = 3.3 V; OE = 0 V, f = 10 MHz S = 0 V or 3.3 V	-	6.5	-	
			V _{CC} = 3.3 V; OE = 0 V, f = 240 MHz S = 0 V or 3.3 V	-	5	-	
C _{OFF}	HSD1n or HSD2n	HSD2n	$V_{CC} = V_{IS} = 3.3 \text{ V};$ $\overline{OE} = 0 \text{ V}, \text{ S} = 3.3 \text{ V or } 0 \text{ V},$ f = 1 MHz	-	3.8	-	pF
			$V_{CC} = V_{IS} = 3.3 \text{ V};$ $\overline{OE} = 0 \text{ V}, \text{ S} = 3.3 \text{ V or } 0 \text{ V},$ f = 10 MHz	-	2.0	-	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.



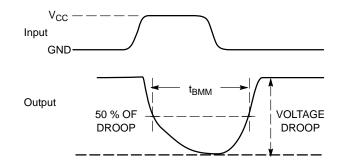
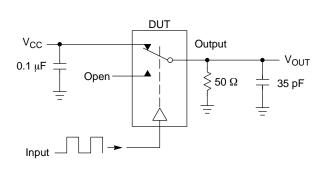


Figure 3. t_{BBM} (Time Break-Before-Make)



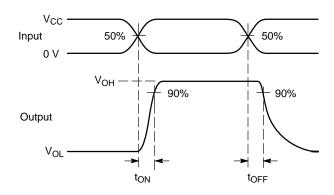
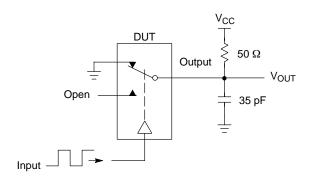


Figure 4. t_{ON}/t_{OFF}



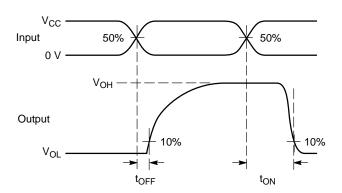
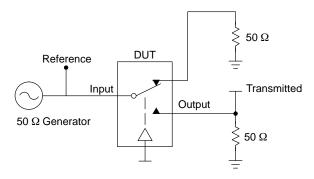


Figure 5. t_{ON}/t_{OFF}



Channel switch control/s test socket is normalized. Off isolation is measured across an off channel. On loss is the bandwidth of an On switch. V_{ISO} , Bandwidth and V_{ONL} are independent of the input signal direction.

$$\begin{split} &V_{ISO} = \text{Off Channel Isolation} = 20 \text{ Log} \left(\frac{V_{OUT}}{V_{IN}} \right) \text{for } V_{IN} \text{ at } 100 \text{ kHz} \\ &V_{ONL} = \text{On Channel Loss} = 20 \text{ Log} \left(\frac{V_{OUT}}{V_{IN}} \right) \text{ for } V_{IN} \text{ at } 100 \text{ kHz to } 50 \text{ MHz} \end{split}$$

Bandwidth (BW) = the frequency 3 dB below V_{ONL}

 V_{CT} = Use V_{ISO} setup and test to all other switch analog input/outputs terminated with 50 Ω

Figure 6. Off Channel Isolation/On Channel Loss (BW)/Crosstalk (On Channel to Off Channel)/V_{ONL}

DETAILED DESCRIPTION

High Speed (480Mbps) USB 2.0 Optimized

The NL3HS2222 is a DPDT switch designed for USB applications within portable systems. The R_{ON} and C_{ON} of both switches are maintained at industry–leading low levels in order to ensure maximum signal integrity for USB 2.0 high speed data communication. The NL3HS2222 switch can be used to switch between high speed (480Mbps) USB signals and a variety of audio or data signals such as full speed USB, UART or even a moderately resistive audio terminal.

Over Voltage Tolerant

The NL3HS2222 features over voltage tolerant I/O protection on the common signal pins D+/D-. This allows the switch to interface directly with a USB connector. The D+/D- pins can withstand a short to V_{BUS} , up to 5.25 V, continuous DC current for up to 24 hours as specified in the USB 2.0 specification. This protection is achieved without the need for any external resistors or protection devices.

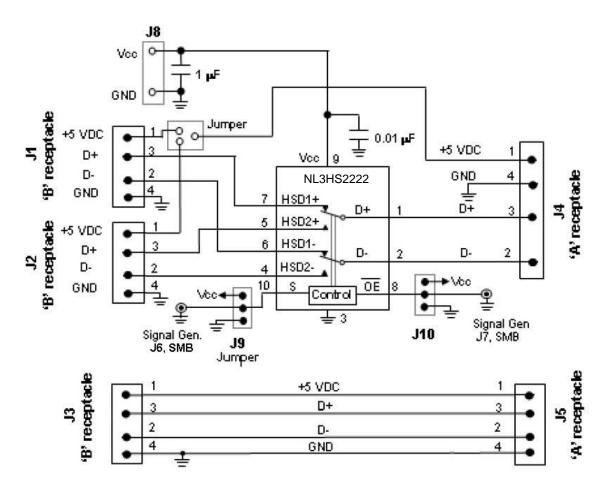


Figure 7. Board Schematic

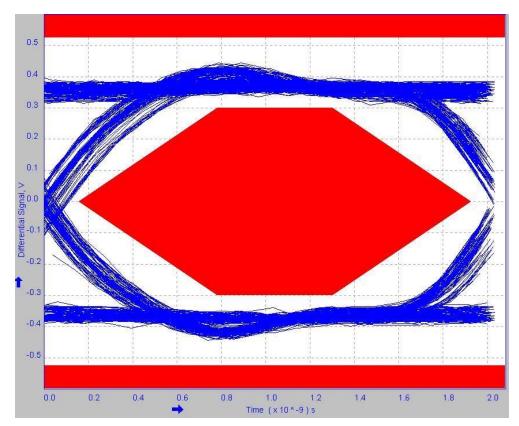


Figure 8. Signal Quality

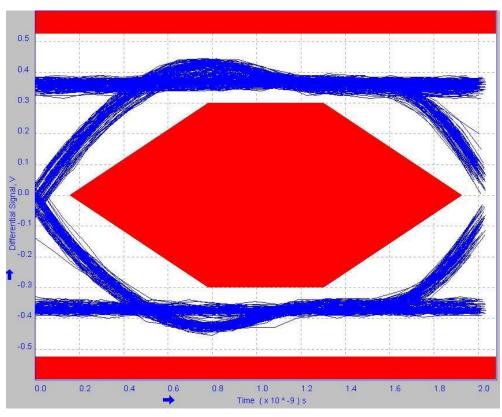


Figure 9. Near End Eye Diagram

Near End Test Data:					Min	Max	
	Consecutive jitter range	-54.37	73.21	ps			
Std.	Paired JK jitter range	-59.14	59.56	ps	–200 ps	+200 ps	
	Paired KJ jitter range	-50.79	34.57	ps			
	Consecutive jitter range	-74.43	81.65	ps			
N.C.	Paired JK jitter range	-61.60	58.55	ps	–200 ps	+200 ps	
	Paired KJ jitter range	-55.31	48.43	ps]		
	Consecutive jitter range	-82.55	80.33	ps			
N.O.	Paired JK jitter range	-53.50	71.65	ps	–200 ps	+200 ps	
	Paired KJ jitter range	-62.60	47.30	ps			

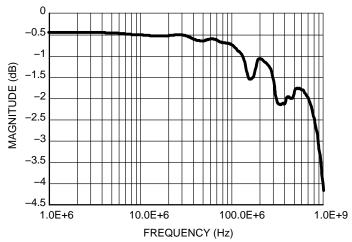


Figure 10. Magnitude vs. Frequency @ V_{CC} = 3.3 V, All Temperatures

I_{CC} Leakage Current as a Function of V_{IN} Voltage (25°C)

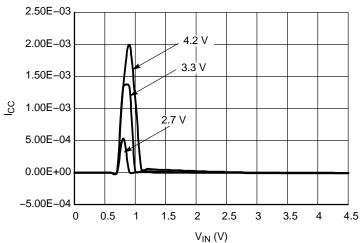
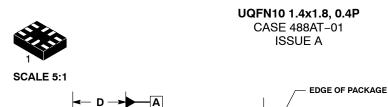


Figure 11. I_{CC} vs. V_{IN} , Select Pin, All V_{CC} 's, 25°C



DATE 01 AUG 2007

NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 CONTROLLING DIMENSION: MILLIMETERS
- 3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.25 AND 0.30 MM
- FROM TERMINAL.

 COPLANARITY APPLIES TO THE EXPOSED PAD
 AS WELL AS THE TERMINALS.

	MILLIMETERS			
DIM	MIN	MAX		
Α	0.45	0.60		
A1	0.00	0.05		
A3	0.127	REF		
b	0.15	0.25		
D	1.40	BSC		
E	1.80 BSC 0.40 BSC			
е				
L	0.30	0.50		
L1	0.00	0.15		
L3	0.40	0.60		

GENERIC MARKING DIAGRAM*



XX = Specific Device Code

= Date Code М

= Pb-Free Package

(Note: Microdot may be in either location)

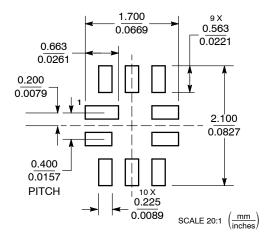
*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

PIN 1 REFERENCE **DETAIL A** 0.10 C **Bottom View** (Optional) 0.10 C MOLD CMPD EXPOSED Cu-В **TOP VIEW** АЗ 0.05 C 0.05 C \triangle **DETAIL B** Α1 SEATING PLANE Side View SIDE VIEW (Optional) 10 X 0.10 C A B Œ

0.05 С

MOUNTING FOOTPRINT

BOTTOM VIEW



		Electronic versions are uncontrolled except when accessed directly from Printed versions are uncontrolled except when stamped "CONTROLLED		
	DESCRIPTION:	10 PIN UQFN, 1.4 X 1.8, 0.4	iP	PAGE 1 OF 1

ON Semiconductor and unare trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. ON Semiconductor does not convey any license under its patent rights nor the rights of others.

onsemi, ONSEMI, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. Onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights nor the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any EDA class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer pu

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Email Requests to: orderlit@onsemi.com

onsemi Website: www.onsemi.com

TECHNICAL SUPPORT North American Technical Support: Voice Mail: 1 800-282-9855 Toll Free USA/Canada Phone: 011 421 33 790 2910

Europe, Middle East and Africa Technical Support:

a Phone: 00421 33 790 2910

For additional information, please contact your local Sales Representative

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for USB Switch ICs category:

Click to view products by ON Semiconductor manufacturer:

Other Similar products are found below:

NLAS7213MUTBG FSA221UMX FSUSB31UMX FSA806UMX NLAS7222AMTR2G NL3S2223MUTBG TC7USB3212WBG(ELAH PI3USB31531ZLCEX PI3USB31532ZLCEX PI5USB31213XEAEX BD91N01NUX-E2 MP5030DGQH-Z NL3S22AHMUTAG NL3S22UHMUTAG FSA9280AUMX NLAS7242MUTBG HD3SS460RHRT TPS2549IRTERQ1 PI2USB4122ZHEX TS5USBC402IYFPT NS5S1153MUTAG FSUSB11MTCX FSUSB42MUX PI3USB102GZLEX P6KE110A SMAJ200A SMAJ70CA SMAJ11A SMAJ140CA SMAJ14A SMAJ160CA SMAJ250A SMAJ51CA SMAJ5.0CA 30KP400CA 1SMB5.0AT3G MAX4717ETB+T MAX4989ETD+T MAX4717EBCT MAX4717EUB+ MAX4906ELB+T MAX4899ETE+ MAX4906EFELB+T MAX4907FELA+T MAX4907ELA+T MAX4983EEVB+T MAX4984EEVB+T MAX4899AEETE+T MAX14618ETA+T MAX14651ETA+T